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Sheet 1 of 1		Application Number		February 8, 2002	
		Filing Date		Shigetaka AOKI	
		First Named Inventor			
		Group Art Unit			
		Examiner Name			
		Attorney Docket Number		740819-744	

  

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		Japan	05-183154			07/23/1993		Abstract
		Japan	04-247664			09/03/1992		Abstract
		Japan	11-233771			08/27/1999		Abstract
		Japan	10-93076			04/10/1998		Abstract

  

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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		S.K. Ray et al. "NOVEL SiGeC CHANNEL HETEROJUNCTION PMOSFET", Technical Digest of International Electron Devices Meeting 1996, pp. 261-264.	
		M. Gluck et al., "Modulation-doped Si <sub>1-x</sub> Ge <sub>x</sub> C <sub>y</sub> p-type Hetero-FETs", Physica E, July 1998, Vol. 2, pp. 768-771.	
		Eduardo Jose Quinones et al. "Design, Fabrication, and Analysis of SiGeC Heterojunction PMOSFETs", IEEE TRANSACTIONS ON ELECTRON DEVICES, September 2000, Vol. 47, No. 9, pp. 1715-1725.	
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